# Supertex inc.

# N-Channel Depletion-Mode Vertical DMOS FET in Single and Dual Options

#### Features

- Very low gate threshold voltage
- Designed to be source-driven
- Low switching losses
- Low effective output capacitance
- Designed for inductive loads
- Well matched for low second harmonic when driven by Supertex MD2130

### Applications

- Medical ultrasound beamforming
- Ultrasonic array focusing transmitter
- Piezoelectric transducer waveform drivers
- High speed arbitrary waveform generator
- Normally-on switches
- Solid state relays
- Constant current sources
- Power supply circuits

### **General Description**

The Supertex DN2625 is a low threshold depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

The DN2625DK6-G contains two MOSFETs in an 8-lead, dual pad DFN package. The DN2625K6-G in the 14-lead QFN package is not recommended for new designs, but may continue to be purchased for existing designs.

		Package Options			I <sub>ns</sub>	
Device	rice TO-252 8-Lead DFN 5.00x5.00mm body (D-PAK) 0.90mm height (max) 1.27mm pitch (dual pa		14-Lead QFN* 5.00x5.00mm body 1.00mm height (max) 1.27mm pitch	BV <sub>DSX</sub> / BV <sub>DGX</sub> (V)	V <sub>GS(OFF)</sub> (max) (V)	(pulsed) (V <sub>GS</sub> = 0.9V) (min) (A)
DN2625	DN2625K4-G	DN2625DK6-G	DN2625K6-G	250	-2.1	3.3

-G indicates package is RoHS compliant ('Green')

This package obsolete. For single MOSFETs use the TO-252 D-PAK (K4), for dual MOSFETs use the 8-Lead DFN (K6) (dual pad).



#### **Absolute Maximum Ratings**

Parameter	Value
Drain-to-source voltage	250V
Drain-to-gate voltage	250V
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Distance of 1.6mm from case for 10 seconds.



for new designs.

#### **Ordering Information**

# DN2625

#### **Product Marking**

Packages may or may not include the following marks: Si or



TO-252 D-PAK (K4)

L = Lot Number YY = Year Sealed WW = Week Sealed A = Assembler ID C = Country of Origin = "Green" Packaging

#### 8-Lead DFN (K6) (dual pad)

DN2625 LLLLLL YYWW AAACCC

L = Lot Number YY = Year Sealed WW = Week Sealed A = Assembler ID Country of Origin = "Green" Packaging

14-Lead QFN (K6)

This package is not recommended for new designs.

#### **Thermal Characteristics** l<sub>D</sub> l<sub>D</sub> $\mathsf{R}_{_{ heta ja}}$ $\mathsf{R}_{_{ heta jc}}$ DRM Package (pulsed) (continuous)1 (°C/W) (°C/W) (A) (A) (A) (A) D-PAK 50² 1.1 3.3 5.5 1.1 3.3 8-Lead DFN (dual pad) 1.1 3.3 **32**³ 3.2 1.1 3.3 14-Lead QFN 1.1 22<sup>3</sup> 2.04 3.3 1.1 3.3

Notes:

1.  $I_{p}$  (Continuous) is limited by max.  $T_{r}$ 

4-layer, 1oz, 3x4inch PCB, with 20-via for drain pad. 2.

4-layer, 1oz, 3x4inch PCB, with 12-via for drain pad. З.

Junction to the DFN thermal pad. 4.

#### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Мах	Units	Conditions				
BV <sub>DSX</sub>	Drain-to-source breakdown voltage	250	-	-	V	V <sub>GS</sub> = -2.5V, Ι <sub>D</sub> = 50μA				
BV <sub>DGX</sub>	Drain-to-gate breakdown voltage	250	-	-	V	V <sub>GS</sub> = -2.5V, Ι <sub>D</sub> = 50μA				
V <sub>GS(OFF)</sub>	Gate-to-source off voltage	-1.5	-	-2.1	V	V <sub>DS</sub> = 15V, Ι <sub>D</sub> = 100μA				
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with temperature	-	-	-4.5	mV/ºC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 100μA				
I <sub>GSS</sub>	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$				
	Drain to course lockage current	-	-	1.0		$V_{_{\rm DS}}$ = 250V, $V_{_{\rm GS}}$ = -5.0V				
D(OFF)	Drain-to-source leakage current	-	-	200	μΑ	$V_{\rm DS}$ = 250V, $V_{\rm GS}$ = -5.0V, $T_{\rm A}$ = 125°C				
I <sub>DSS</sub>	Saturated drain-to-source current	1.1	-	-	А	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V				
I <sub>DS(PULSE)</sub>	Pulsed drain-to-source current	3.1	3.3	-	А	$V_{GS} = 0.9V, V_{DS} = 15V$ (with duty cycle of 1%)				
R <sub>DS(ON)</sub>	Static drain-to-source on-resistance		-	3.5	Ω	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0A				
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.1	%/°C	V <sub>GS</sub> = 0V, I <sub>D</sub> = 200mA				
G <sub>FS</sub>	Forward transconductance	100	-	-	mmho	V <sub>DS</sub> = 10V, I <sub>D</sub> = 150mA				
C <sub>ISS</sub>	Input capacitance	-	800	1000		$V_{cc} = -2.5V_{c}$				
C <sub>oss</sub>	Common source output capacitance	-	70	210	pF	$V_{\rm DS}^{\rm GS} = 25V,$				
C <sub>RSS</sub>	Reverse transfer capacitance	-	18	70		f = 1.0MHz				
t <sub>d(ON)</sub>	Turn-on delay time	-	-	10		V = 25V				
t,	Rise time	-	-	20	20	$I_{\rm D} = 150 {\rm mA},$				
t <sub>d(OFF)</sub>	Turn-off delay time	-	-	10	115	$R_{GEN} = 3.0\Omega,$				
t <sub>r</sub>	Fall time		-	20		$V_{gs} = 0v \text{ to } -10V$				
V <sub>SD</sub>	Diode forward voltage drop	-	-	1.8	V	V <sub>GS</sub> = -2.5V, I <sub>SD</sub> = 150mA				
$Q_{G}$	Total gate charge	-	-	7.04		I <sub>2</sub> = 3.5A,				
Q <sub>GS</sub>	Gate-to-source charge	-	-	0.783	nC	$V_{DS} = 100V,$ $V_{GS} = 1.5V$				
$Q_{GD}$	Gate-to-drain charge	-	-	3.73						

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## DN2625

#### **Switching Waveforms and Test Circuit**



# **Typical Performance Curves**





**Transfer Characteristics** 



#### **Saturation Characteristics**







### Typical Performance Curves (cont.)

**On-Resistance vs Drain Current** 

#### 5.0 $V_{GS} = 1V$ 4.5 4.0 3.5 $R_{_{DS(ON)}}$ (ohms) 3.0 2.5 2.0 1.5 1.0 0.5 0.0 0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 5.5 $I_{_{D}}(A)$





Transconductance vs Drain Current



# 3-Lead TO-252 D-PAK Package Outline (K4)



#### Note:

1. Although 4 terminal locations are shown, only 3 are functional. Lead number 2 was removed.

Symb	ol	Α	A1	b	b2	b3	c2	D	D1	E	E1	е	н	L	L1	L2	L3	L4	L5	θ	<b>01</b>
Dimen- sion N (inches) N	MIN	.086	.000*	.025	.030	.195	.018	.235	.205	.250	.170		.370	.055			.035	.025*	.045	<b>0</b> <sup>0</sup>	<b>0</b> <sup>0</sup>
	NOM	-	-	-	-	-	-	.240	-	-	-	.090 BSC	-	.060	.108 REF	.020 BSC	-	-	-	-	-
	MAX	.094	.005	.035	.045	.215	.035	.245	.217*	.265	.182*		.410	.070			.050	.040	.060	10º	15 <sup>0</sup>

JEDEC Registration TO-252, Variation AA, Issue E, June 2004.

\* This dimension is not specified in the JEDEC drawing.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO252K4, Version E041309.

## DN2625

### 8-Lead DFN Package Outline (K6) 5.00x5.00mm body, 0.90mm height (max), 1.27mm pitch (dual pad)



#### Notes:

- 1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.
- 2. Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

Symbol		Α	A1	A3	b	D	D2	E	E2	е	K1	L	L1	θ
Dimension (mm)	MIN	0.80	0.00	0.20 REF	0.35	4.90	1.93	4.90	1.90	1.27 BSC	0.40 REF	0.40	0.00	0°
	NOM	0.85	-		0.40	5.00	2.03	5.00	2.00			0.50	-	-
	MAX	0.90	0.05		0.45	5.10	2.13	5.10	2.10			0.60	0.15	14 <sup>0</sup>

Drawings not to scale

Supertex Doc. #: DSPD-8DFNK65x5P127, Version A040209



### 14-Lead QFN Package Outline (K6) 5.00x5.00mm body, 1.00mm height (max), 1.27mm pitch

#### Notes:

1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

Symbol		Α	A1	A3	b	D	D2	E	E2	е	AA	BB	CC	DD	θ
Dimension (mm)	MIN	0.80	0.00	0.20 REF	0.46	4.85	4.45	4.85	2.52	1.27 BSC	0.152	0.473	0.66	0.456	<b>0</b> 0
	NOM	0.90	0.02		0.51	5.00	4.50	5.00	2.57		0.252	0.523	0.71	0.506	-
	MAX	1.00	0.05		0.58	5.15	4.55	5.15	2.62		0.352	0.583	0.77	0.566	14 <sup>0</sup>

Drawings not to scale.

Supertex Doc. #: DSPD-14QFNK65X5P127, Version B090808.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>http://www.supertex.com/packaging.html</u>.)

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